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Optimization of Series Resistance in Sub-0.2 um SOI MOSFET's, IEEE Electron Device letters, VOL. 15, No. 9, September 1994, p. 363-365. Optimization of series resistance in Sub-0.2 um SOI MOSFET's, 1993 IEEE, pp. IEDM93-723-726-IEDM 93. C RAMINER A CONSIDERED DATE CONSIDERED CRAMINER A CONSIDERED CRAMINER CRAMINER A CONSIDERED	J. SADI	Deep sub-0.1 um MOSFET's with Very Thin SOL Layer for Ultra-Low Power Applicants, Information and Communication			
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